

### Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

### Listing of Claims

1. (Canceled)

2. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;  
forming a mask over the ~~said~~ semiconductor film wherein the mask has at least two openings to expose having a first region and a second region of the semiconductor film;

simultaneously providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask; and

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein crystals grow from said first region to said second region and the growth of the crystals terminates at said second region.

3. (Previously Presented) The method according to claim 2 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

4. (Currently Amended) A method of manufacturing an electroluminescence device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;  
forming a mask over the ~~said~~ semiconductor film wherein the mask has at least two openings to expose having a first region and a second region of the semiconductor film;

simultaneously providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask; and

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein crystals grow from said first region to said second region and the growth of the crystals terminates at said second region.

5. (Previously Presented) The method according to claim 4 wherein said metal is selected from the group consisting of Fe, C, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

6. (Currently Amended) A method manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;  
forming a mask over the ~~said~~ semiconductor film wherein the mask has at least two openings to expose having a first region and a second region of the semiconductor film;

simultaneously providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask; and

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein crystals grow from said first region substantially in parallel to said insulating surface,

wherein said second region functions as a stopper for terminating the crystallization from said first region.

7. (Previously Presented) The method according to claim 6 wherein said metal is selected from the group consisting of Fe, C, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

8. (Currently Amended) A method of manufacturing an electroluminescence display device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;  
forming a mask over the said semiconductor film wherein the mask has at least two openings to expose having a first region and a second region of the semiconductor film;  
simultaneously providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask; and

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein crystals grow from said first region substantially in parallel to said insulating surface, and

wherein said second region functions as a stopper for terminating the crystallization from said first region.

9. (Previously Presented) The method according to claim 8 wherein said metal is selected from the group consisting of Fe, C, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

10. (Currently Amended) A method of manufacturing a semiconductor device comprising the step of:

forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having a first stripe-shaped region and a second stripe-shaped region arranged in parallel with each other;

forming a mask over the semiconductor film wherein the mask has at least two openings to expose the first stripe-shaped region and the second stripe-shaped region of the semiconductor film;

simultaneously providing said first and second stripe-shaped regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask; and

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein widths of said first and second stripe-shaped regions are different from each other, and

wherein said second stripe-shaped region functions as a stopper for terminating the crystallization from said first stripe-shaped region.

11. (Previously Presented) The method according to claim 10 wherein said metal is selected from the group consisting of Fe, C, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

12. (Currently Amended) A method of manufacturing an electroluminescence display device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having a first stripe-shaped region and a second stripe-shaped region arranged in parallel with each other;

forming a mask over the semiconductor film wherein the mask has at least two openings to expose the first stripe-shaped region and the second stripe-shaped region of the semiconductor film;

simultaneously providing said first and second stripe-shaped regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask; and

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein widths of said first and second stripe-shaped regions are different from each other, and

wherein said second stripe-shaped region functions as a stopper for terminating the crystallization from said first stripe-shaped region.

13. (Previously Presented) The method according to claim 12 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

14. (Previously Presented) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having at least first, second and third stripe-shaped regions arranged in parallel with one another wherein said second stripe-shaped region is located between said first and third stripe-shaped regions;

simultaneously providing said first, second and third stripe-shaped regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film; and

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein a width of said second stripe-shaped region is smaller than widths of said first and third stripe-shaped regions, and

wherein said second stripe-shaped region functions as a stopper for terminating the crystallization from said first stripe-shaped region.

15. (Previously Presented) The method according to claim 14 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Pr, Pd, Os, Ir, Pt, Cu and Au.

16. (Previously Presented) A method of manufacturing an electroluminescence display device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having at least first, second and third stripe-shaped regions arranged in parallel with one another wherein said second stripe-shaped region is located between said first and third stripe-shaped regions;

simultaneously providing said first, second and third stripe-shaped regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film; and

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein a width of said second stripe-shaped region is smaller than widths of said first and third stripe-shaped regions, and

wherein said second stripe-shaped region functions as a stopper for terminating the crystallization from said first stripe-shaped region.

17. (Previously Presented) The method according to claim 16 wherein said metal is selected from the group consisting of Fe, C, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.